

**IN THE CLAIMS:**

Claim 1 (Currently Amended): A wire comprising a Cu (copper) layer contacted along at least one surface by a first coating film made of titanium and contacted along at least the remaining three side surfaces by a second coating film made of titanium oxide.

Claim 2 (Withdrawn): A wiring comprising a Cu layer surrounded by a coating film made of molybdenum or molybdenum oxide.

Claim 3 (Withdrawn): A wiring comprising a Cu layer surrounded by a coating film made of chromium or chromium oxide.

Claim 4 (Withdrawn): A wiring comprising a Cu layer surrounded by a coating film made of tantalum or tantalum oxide.

Claim 5 (Withdrawn): A wiring as claimed in claim 1, wherein the coating film includes a titanium oxide.

Claim 6 (Withdrawn): A wiring as claimed in claim 1, wherein the coating film includes a titanium film formed around the Cu layer, and a film which is made of titanium oxide and is formed on the surface of the titanium film.

Claim 7 (Withdrawn): A wiring as claimed in claim 1, wherein the coating film includes a titanium film provided at a portion of the circumferential area of the Cu layer, and a film which is provided at the remaining portion of the circumferential area of the Cu layer and is made of titanium oxide.

Claim 8 (Withdrawn): A wiring as claimed in claim 3, wherein the coating film includes a chromium film and a film made of chromium oxide.

Claim 9 (Withdrawn): A wiring as claimed in claim 3, wherein the coating film includes a chromium film formed around the Cu layer; and a film which is made of chromium oxide and is formed on the surface of the chromium film.

Claim 10 (Withdrawn): A wiring as claimed in claim 3, wherein the coating film includes a chromium film provided at a portion of the circumferential area of the Cu layer, and a film which is provided at the remaining portion of the circumferential area of the Cu layer and is made of chromium oxide.

Claim 11 (Previously Presented): A TFT (thin film transistor) substrate having a wire as claimed in claim 1.

Claim 12 (Withdrawn): A TFT substrate comprising a base and a wiring as claimed in claim 1 which is formed on the base via a TiN film.

Claim 13 (Withdrawn): A TFT substrate comprising a base and a wiring comprising a Cu layer and a coating film made of titanium or titanium oxide which is formed on the surface of the Cu layer, wherein the wiring is provided on the base via a TiN film.

Claim 14 (Withdrawn): A TFT substrate as claimed in claim 13, wherein the coating film of the wiring includes a titanium film formed around the Cu layer, and a film which is made of titanium oxide and is formed on the surface of the titanium film.

Claim 15 (Withdrawn): A method of manufacturing a TFT substrate, comprising the steps of:

forming a Cu film on a metallic film using a target made of Cu, wherein the metallic film is formed on a base and is made of a metal selected from the group consisting of titanium, molybdenum, chromium, and tantalum;

patterned-processing the Cu film and the metallic film to make a wiring having a desired shape; and

annealing-processing the base so as to form a metallic coating film on the patterning-processed Cu film, wherein the metallic coating film is made of a metal selected from the group consisting of titanium, molybdenum, chromium, and tantalum;

Claim 16 (Withdrawn): A method of manufacturing a TFT substrate, comprising the steps of:

    forming a TiN film on a base;  
    forming a film made of titanium or titanium oxide on the TiN film;  
    forming a Cu film on the film made of titanium or titanium oxide by using a target made of Cu, so that a multi-layered film is formed;  
    patterning-processing the multi-layered film to make a wiring having a desired shape; and  
    annealing-processing the base so as to form a coating film made of titanium or titanium oxide on the patterning-processed Cu film.

Claim 17 (Withdrawn): A method of manufacturing a TUFT substrate, as claimed in claim 16, wherein the thickness of the film made of titanium or titanium oxide formed on the tin is 10 to 20 nm.

Claim 18 (Withdrawn): A method of manufacturing a TUFT substrate, as claimed in claim 15 or 16, wherein the coating film includes oxygen.

Claim 19 (Withdrawn): A method of manufacturing a TUFT substrate, as claimed in claim 16, wherein a titanium oxide layer, which is generated on the surface of the film made of titanium or titanium oxide before the Cu film is formed, is removed by plasma etching.

Claim 20 (Previously Presented): An LCD (liquid crystal display) comprising a pair of opposing substrates and a liquid crystal disposed between the opposing substrates, wherein at least one of the pair of opposing substrates is a TFT substrate as claimed in claim 11.

Claim 21 (Withdrawn): The wiring according to claim 1, wherein the Cu (copper) layer is surrounded along at least four sides by the first coating film.